Mustafa Alevli

List of Publications by Year
in descending order

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29	648	687363 13	552781 26
papers	citations	h-index	g-index

30	30	30	677
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Structural properties of AlN films deposited by plasmaâ€enhanced atomic layer deposition at different growth temperatures. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 266-271.	1.8	111
2	Self-limiting low-temperature growth of crystalline AlN thin films by plasma-enhanced atomic layer deposition. Thin Solid Films, 2012, 520, 2750-2755.	1.8	86
3	Atomic layer deposition of GaN at low temperatures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, 01A124.	2.1	62
4	The influence of N2/H2 and ammonia N source materials on optical and structural properties of AlN films grown by plasma enhanced atomic layer deposition. Journal of Crystal Growth, 2011, 335, 51-57.	1.5	47
5	Characterization of InN layers grown by high-pressure chemical vapor deposition. Applied Physics Letters, 2006, 89, 112119.	3.3	39
6	Optical properties of AlN thin films grown by plasma enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2012, 30, .	2.1	33
7	A Near-Infrared Range Photodetector Based on Indium Nitride Nanocrystals Obtained Through Laser Ablation. IEEE Electron Device Letters, 2014, 35, 936-938.	3.9	33
8	Enhanced memory effect via quantum confinement in 16â€‰nm InN nanoparticles embedded in ZnO charge trapping layer. Applied Physics Letters, 2014, 104, 253106.	3.3	27
9	Comparison of trimethylgallium and triethylgallium as â€œGaâ€•source materials for the growth of ultrathin GaN films on Si (100) substrates via hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 01A137.	2.1	24
10	The characterization of InN growth under high-pressure CVD conditions. Physica Status Solidi (B): Basic Research, 2005, 242, 2985-2994.	1.5	23
11	Substrate temperature influence on the properties of GaN thin films grown by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	19
12	Surface electron accumulation in indium nitride layers grown by high pressure chemical vapor deposition. Surface Science, 2007, 601, L120-L123.	1.9	18
13	Role of film thickness on the structural and optical properties of GaN on Si (100) grown by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	17
14	Generation of InN nanocrystals in organic solution through laser ablation of high pressure chemical vapor deposition-grown InN thin film. Journal of Nanoparticle Research, 2012, 14, 1.	1.9	13
15	Influence of N2/H2 and N2 plasma on binary III-nitride films prepared by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	13
16	The Fermi level dependence of the optical and magnetic properties of Ga1â^'xMnxN grown by metalâ€“organic chemical vapour deposition. Journal of Physics Condensed Matter, 2006, 18, 2615-2622.	1.8	12
17	Performance improvements of ultraviolet/infrared dual-band detectors. Infrared Physics and Technology, 2007, 50, 142-148.	2.9	12
18	Surface structure, composition, and polarity of indium nitride grown by high-pressure chemical vapor deposition. Applied Physics Letters, 2006, 88, 122112.	3.3	11

#	Article	IF	Citations
19	Thermal stability of InN epilayers grown by high pressure chemical vapor deposition. Applied Surface Science, 2013, 268, 1-5.	6.1	11
20	Optical properties of InN grown on templates with controlled surface polarities. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 2351-2354.	1.8	7
21	Enhancement of polycrystalline silicon solar cells efficiency using indium nitride particles. Journal of Optics (United Kingdom), 2015, 17, 105903.	2.2	7
22	Enhancement in c-Si solar cells using 16 nm InN nanoparticles. Materials Research Express, 2016, 3, 056202.	1.6	6
23	Effect of N2/H2 plasma on the growth of InN thin films on sapphire by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	6
24	Visible/infrared refractive index and phonon properties of GaN films grown on sapphire by hollow-cathode plasma-assisted atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2019, 37, 050901.	2.1	5
25	Effect of reactor pressure on optical and electrical properties of InN films grown by high-pressure chemical vapor deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 423-429.	0.8	3
26	Properties of InN grown by High-Pressure CVD. Materials Research Society Symposia Proceedings, 2005, 892, 64.	0.1	1
27	Effect of substrate temperature and Ga source precursor on growth and material properties of GaN grown by hollow cathode plasma assisted atomic layer deposition. , 2016, , .		1
28	The growth of InN and related alloys by high-pressure CVD. , 2005, , .		0
29	Properties of InN layers grown by High Pressure CVD. Materials Research Society Symposia Proceedings, 2006, 955, 1.	0.1	0